

ESD7205

ESD Protection Diode

Low Capacitance ESD Protection Diodes for High Speed Data Line

The ESD7205 ESD protection diode array is designed to protect high speed data lines from ESD. Ultra-low capacitance and low ESD clamping voltage make this device an ideal solution for protecting voltage sensitive high speed data lines. The small form factor, flow-through style package allows for easy PCB layout and matched trace lengths necessary to maintain consistent impedance between high speed differential lines such as Ethernet and LVDS present in automotive camera modules.

Features

- Low Capacitance (0.4 pF Typical, I/O to GND)
- Diode capacitance matching
- Protection for the Following IEC Standards:
IEC 61000-4-2 Level 4 (ESD)
- Low ESD Clamping Voltage (12 V Typical, +16 A TLP, I/O to GND)
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Typical Applications

- 100BASE-T1 / OPEN Alliance BroadR-Reach Automotive Ethernet
- 10/100/1000BASE-T1 Ethernet
- LVDS
- Automotive USB 2.0/3.0
- High Speed Differential Pairs

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	T _J	-55 to +150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature - Maximum (10 Seconds)	T _L	260	°C
IEC 61000-4-2 Contact	ESD	±25	kV
IEC 61000-4-2 Air		±25	
ISO 10605 330 pF / 330 Ω Contact		±20	
ISO 10605 330 pF / 2 kΩ Contact		±30	
ISO 10605 150 pF / 2 kΩ Contact		±30	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



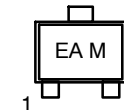
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MARKING DIAGRAMS



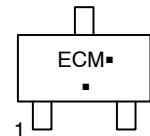
SOT-723
CASE 631AA



EA = Specific Device Code
M = Date Code



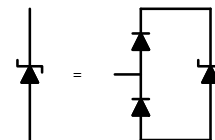
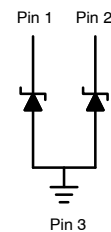
SC-70
CASE 419



EC = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

PIN CONFIGURATION AND SCHEMATIC



ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

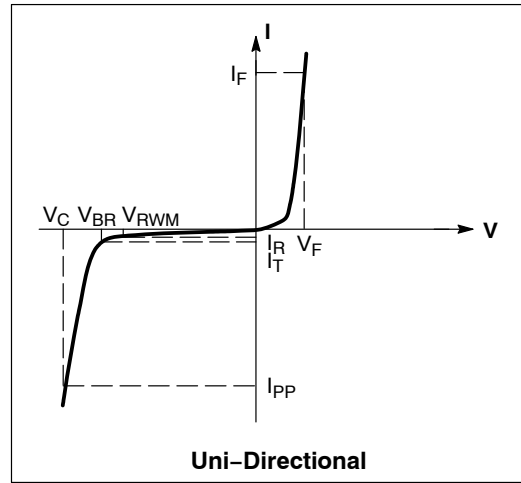
ESD7205

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current

*See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}	I/O Pin to GND			5.0	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{ mA}$, I/O Pin to GND	5.2	6.0	8.0	V
Reverse Leakage Current	I_R	$V_{RWM} = 5.0\text{ V}$, I/O Pin to GND			1	μA
Clamping Voltage (Note 1)	V_C	IEC61000-4-2, $\pm 8\text{ kV}$ Contact	See Figures 3 and 4			
Clamping Voltage TLP (Note 2)	V_C	$I_{PP} = 8\text{ A}$ $I_{PP} = 16\text{ A}$ $I_{PP} = -8\text{ A}$ $I_{PP} = -16\text{ A}$		10 12.5 -4.0 -8.0		V
Junction Capacitance Match	ΔC_J	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$ between I/O1 to GND and I/O2 to GND		5	10	%
Junction Capacitance	C_J	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$ between I/O Pins and GND ESD7205DT5G ESD7205WTT1G		0.34 0.47	0.55 0.85	μF
		$V_R = 0\text{ V}$, $f = 1\text{ MHz}$ between I/O Pins ESD7205DT5G ESD7205WTT1G		0.20 0.23	0.35 0.40	
3dB Bandwidth	f_{BW}	$R_L = 50\ \Omega$		5		GHz

- For test procedure see Figures 5 and 6 and application note AND8307/D.
- ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model.
TLP conditions: $Z_0 = 50\ \Omega$, $t_p = 100\text{ ns}$, $t_r = 4\text{ ns}$, averaging window; $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$.

ESD7205

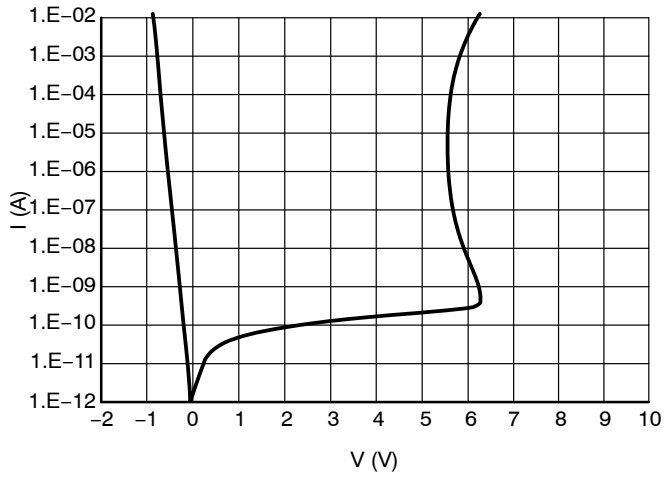


Figure 1. IV Characteristics

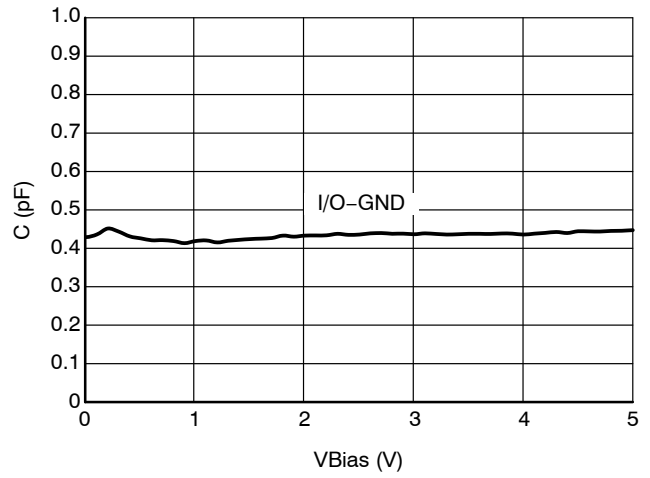


Figure 2. CV Characteristics

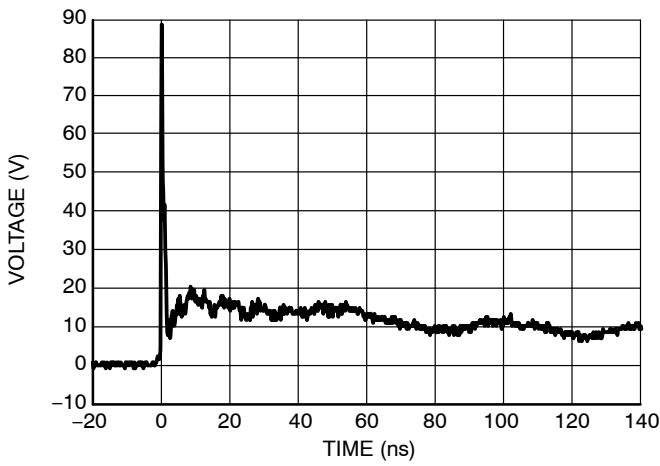


Figure 3. IEC61000-4-2 +8 kV Contact ESD Clamping Voltage

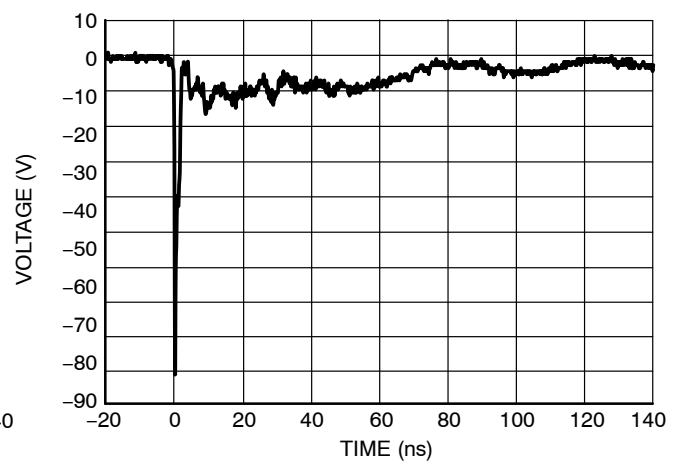


Figure 4. IEC61000-4-2 -8 kV Contact ESD Clamping Voltage

ESD7205

IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8



Figure 5. IEC61000-4-2 Spec

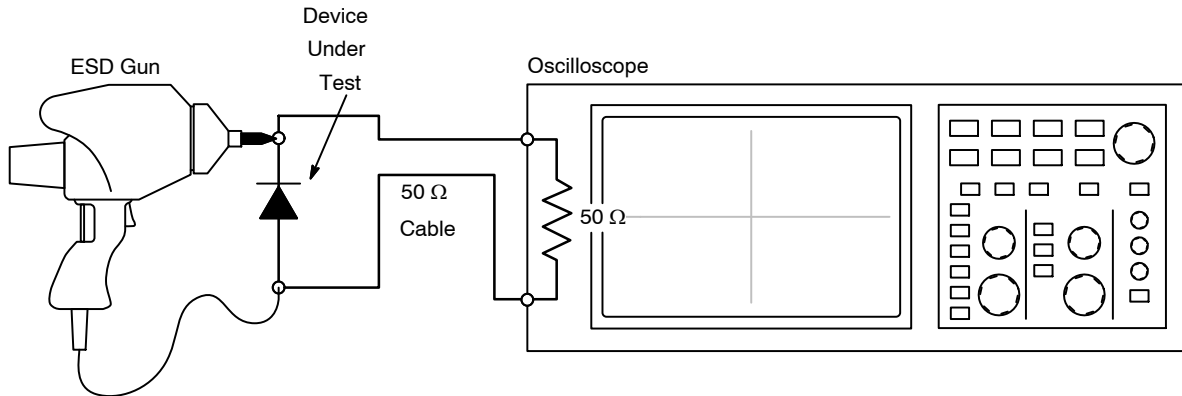


Figure 6. Diagram of ESD Clamping Voltage Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

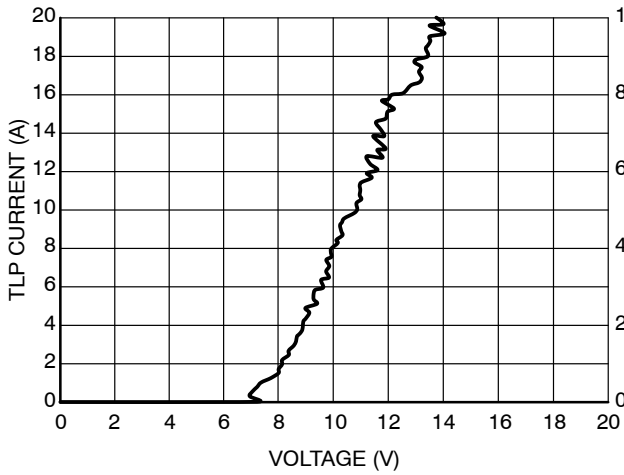


Figure 7. Positive TLP IV Curve

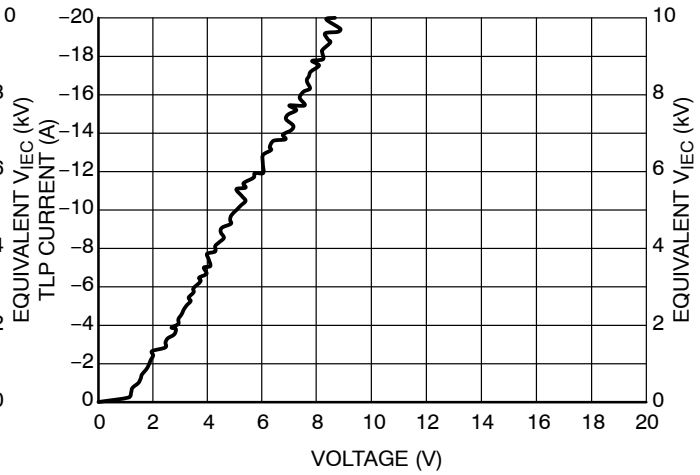


Figure 8. Negative TLP IV Curve

NOTE: TLP parameter: $Z_0 = 50 \Omega$, $t_p = 100 \text{ ns}$, $t_r = 300 \text{ ps}$, averaging window: $t_1 = 30 \text{ ns}$ to $t_2 = 60 \text{ ns}$.

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I-V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 9. TLP I-V curves of ESD protection devices accurately demonstrate the product’s ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 10 where an 8 kV IEC 61000-4-2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I-V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

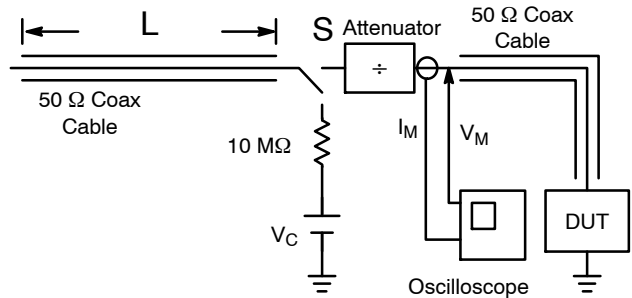


Figure 9. Simplified Schematic of a Typical TLP System

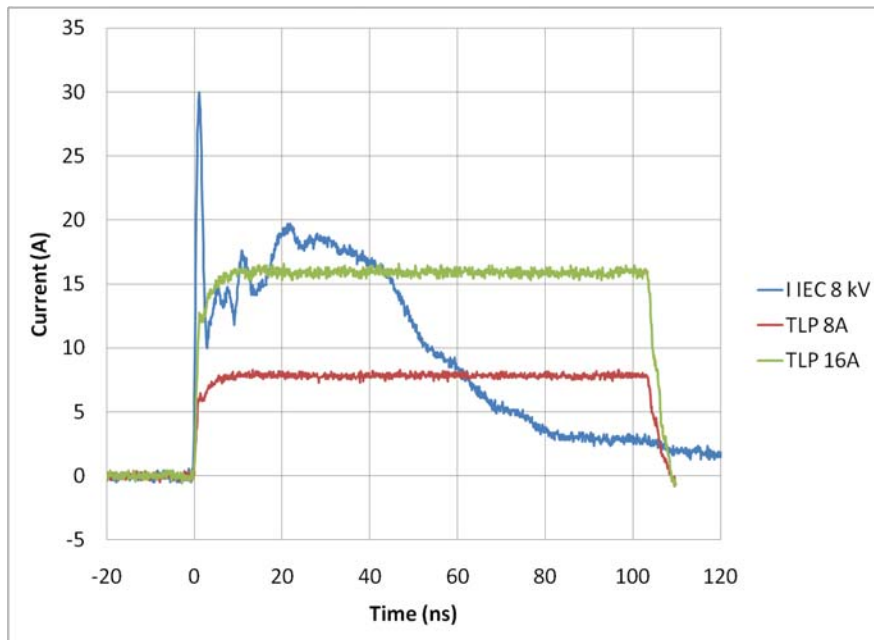


Figure 10. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

ESD7205

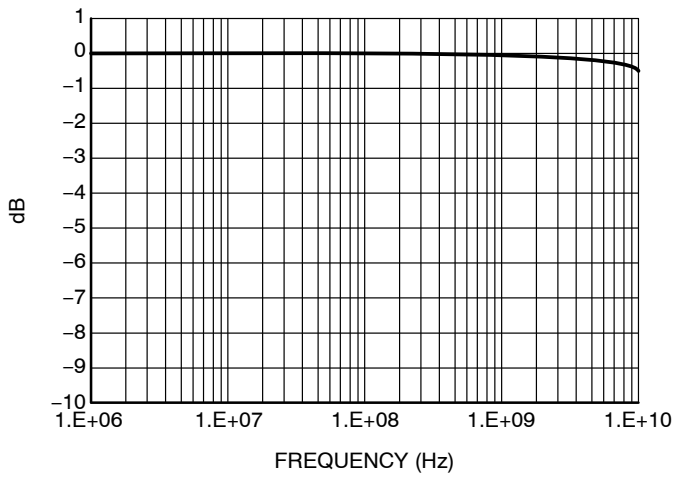


Figure 11. RF Insertion Loss

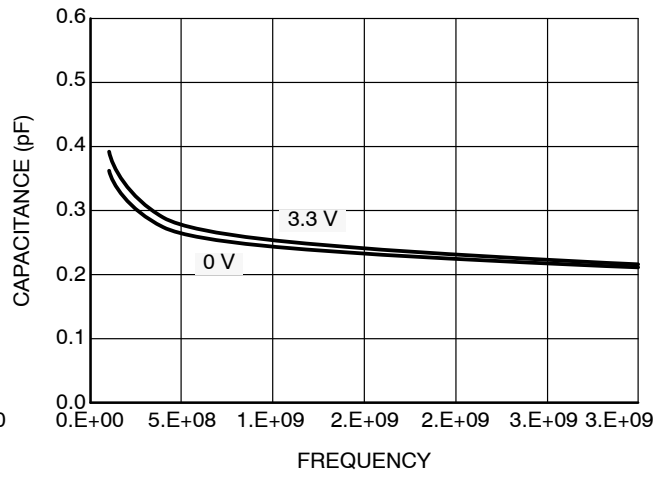


Figure 12. Capacitance over Frequency

ORDERING INFORMATION

Device	Package	Shipping [†]
ESD7205DT5G	SOT-723 (Pb-Free)	8000 / Tape & Reel
SZESD7205DT5G*	SOT-723 (Pb-Free)	8000 / Tape & Reel
ESD7205WTT1G	SOT-323 (Pb-Free)	3000 / Tape & Reel
SZESD7205WTT1G*	SOT-323 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



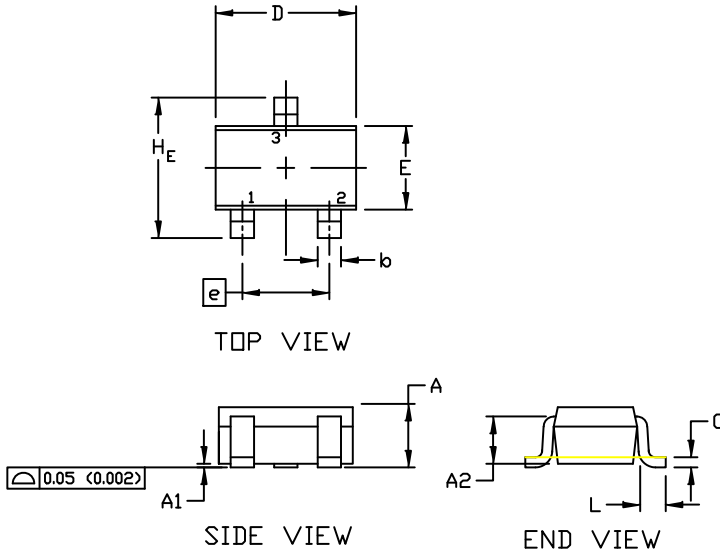
SCALE 4:1

SC-70 (SOT-323)
CASE 419
ISSUE P

DATE 07 OCT 2021

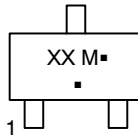
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH



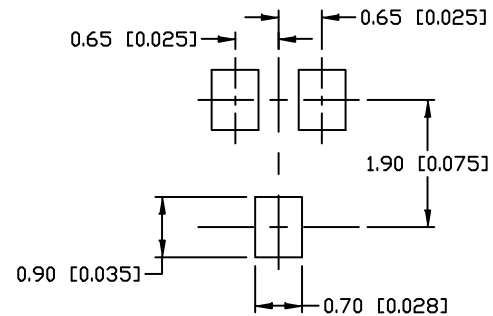
DIM	MILLIMETERS			INCHES		
	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC
MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the [DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D](#).

SOLDERING FOOTPRINT

- | | | | | | |
|---|---|---|--|---|---|
| STYLE 1:
CANCELLED | STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE | STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE | |
| STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE | STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE |

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

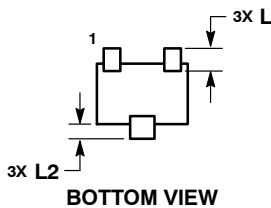
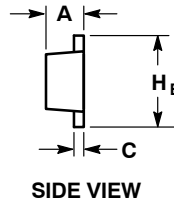
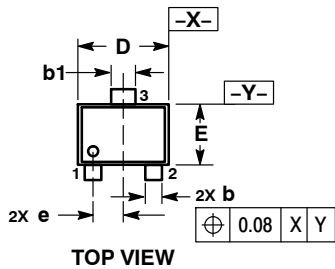
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SOT-723
CASE 631AA-01
ISSUE D

DATE 10 AUG 2009

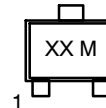


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

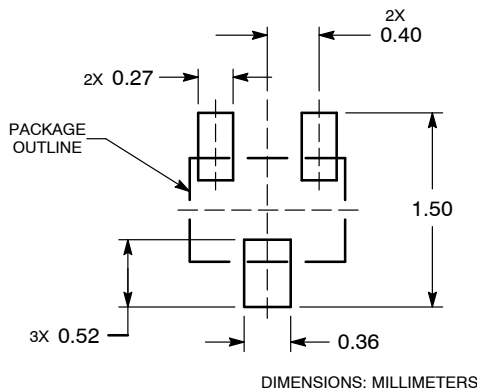
GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

- | | | | | |
|---|--|--|--|--|
| STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE | STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN |
|---|--|--|--|--|

RECOMMENDED SOLDERING FOOTPRINT*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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